MMBTA92L, SMMBTA92L, MMBTA93L

High Voltage Transistors

PNP Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	92	93	Unit
Collector – Emitter Voltage	V_{CEO}	-300	-200	Vdc
Collector - Base Voltage	V _{CBO}	-300	-200	Vdc
Emitter-Base Voltage	ase Voltage V _{EBO} -5.0		-5.0	Vdc
Collector Current — Continuous	Ic	–500 m		mAdc

DEVICE MARKING

MMBTA92L, SMMBTA92L = 2D; MMBTA93LT1 = 2E

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^{\circ}C$	P _D	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation (Note 2) Alumina Substrate, (2) T _A = 25°C	P _D	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	–55 to +150	°C

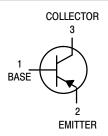
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

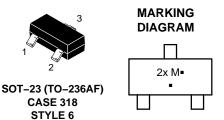
- 1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



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2x = Specific Device Code

M = Date Code*

= Pb–Free Package

(*Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBTA92LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
SMMBTA92LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBTA92LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
SMMBTA92LT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel
MMBTA93LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA92L, SMMBTA92L, MMBTA93L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic			Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 3) $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	MMBTA92, SMMBTA92 MMBTA93	V _{(BR)CEO}	-300 -200		Vdc
Collector – Base Breakdown Voltage (I _C = –100 μAdc, I _E = 0)	MMBTA92, SMMBTA92 MMBTA93	V _{(BR)CBO}	-300 -200	- -	Vdc
Emitter – Base Breakdown Voltage ($I_E = -100 \mu Adc$, $I_C = 0$)		V _{(BR)EBO}	-5.0	-	Vdc
Collector Cutoff Current $(V_{CB} = -200 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -160 \text{ Vdc}, I_E = 0)$	MMBTA92, SMMBTA92 MMBTA93	I _{CBO}	- -	-0.25 -0.25	μAdc
Emitter Cutoff Current $(V_{EB} = -3.0 \text{ Vdc}, I_C = 0)$		I _{EBO}	-	-0.1	μAdc
ON CHARACTERISTICS (Note 3)					
DC Current Gain ($I_C = -1.0 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$) ($I_C = -10 \text{ mAdc}$, $V_{CE} = -10 \text{ Vdc}$)	Both Types Both Types	h _{FE}	25 40	- -	-
$(I_C = -30 \text{ mAdc}, V_{CE} = -10 \text{ Vdc})$	MMBTA92, SMMBTA92 MMBTA93		25 25	- -	
Collector – Emitter Saturation Voltage (I _C = -20 mAdc, I _B = -2.0 mAdc)	MMBTA92, SMMBTA92 MMBTA93	V _{CE(sat)}	- -	-0.5 -0.5	Vdc
Base–Emitter Saturation Voltage (I _C = -20 mAdc, I _B = -2.0 mAdc)		V _{BE(sat)}	-	-0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS		•			
Current – Gain — Bandwidth Product (I _C = –10 mAdc, V _{CE} = –20 Vdc, f = 100 MHz)		f⊤	50	-	MHz
Collector-Base Capacitance (V _{CB} = -20 Vdc, I _E = 0, f = 1.0 MHz)	MMBTA92, SMMBTA92 MMBTA93	C _{cb}		6.0 8.0	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

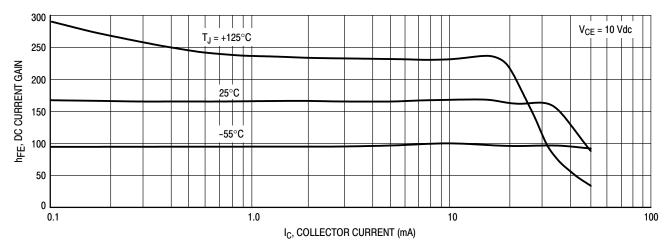
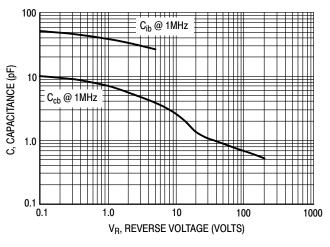


Figure 1. DC Current Gain

MMBTA92L, SMMBTA92L, MMBTA93L



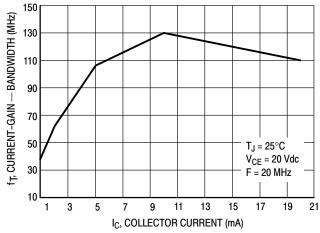
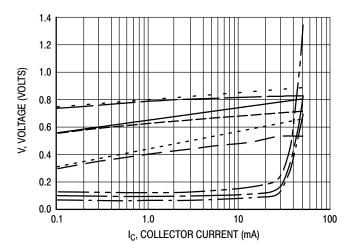


Figure 2. Capacitance

Figure 3. Current-Gain - Bandwidth



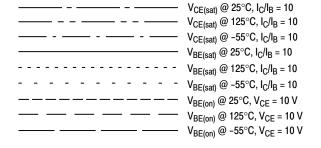


Figure 4. "ON" Voltages

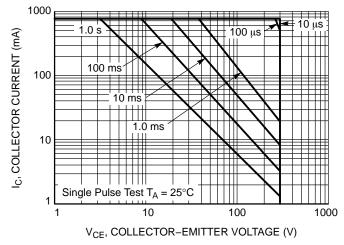


Figure 5. Safe Operating Area



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
ANODE	SOURCE	CATHODE	CATHODE	2. DRAIN	2. GATE
CATHODE	3. GATE	CATHODE-ANODE	ANODE	3. GATE	ANODE

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
CATHODE	CATHODE	2. ANODE	CATHODE	2. ANODE	ANODE
ANODE	CATHODE	CATHODE	ANODE	CATHODE-ANOD	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
SOURCE	OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	NO CONNECTION

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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